

Aplikasi Struk Spbu Full Version

ORDER PEMBELIAN

Tanggal: Dec-09-2011
No. SO: SO112121221
Total Qty: 20000
Jumlah Trans.: 2
Termin: 0 Hari

ID BBM/Item:
Nama BBM/Item:
Supplier: Pertamina
Hrg Beli: 0 Hrg Jual:
Qty: 0
PPh: 25000 Fee: 30000

Cari SO Hapus SO

Jumlah TOTAL **87,950,000**

Daftar Item Pembelian

ID ITEM	NAMA ITEM	SUPPLIER	HARGA	QTY	JUMI
11227	PREMIUM	Pertamina	4,295	10000	42,950
4567	SOLAR	Pertamina	4,500	10000	45,000

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The smallest number of users who use this product is: The present invention relates to a semiconductor memory device, and more particularly to a nonvolatile semiconductor memory device in which data stored in a memory cell array is rewritten with high efficiency. In an electrically erasable and programmable read only memory (EEPROM) as one of nonvolatile semiconductor memory devices, a memory cell array is constituted by a plurality of memory cells (EEPROM cells) each including a nonvolatile memory cell of a stacked gate type or a split gate type. In an EEPROM, data is stored in the memory cell array by injecting an electron into a floating gate of each memory cell. A data write operation in this case is executed by applying a high voltage to a control gate of the memory cell and applying a high voltage to a drain region thereof. As a result, a high electric field is applied to a tunnel oxide film at an interface between the floating gate and the drain region, so that the electron is injected from the drain region into the floating gate. A data erase operation in this case is executed by applying a high voltage to the control gate of the memory cell and applying a high voltage to a source region thereof. As a result, a high electric field is applied to a tunnel oxide film at an interface between the source region and a substrate. Thus, the electron existing in the floating gate is discharged from the floating gate into the source region. On the other hand, in an EEPROM, data is stored in the memory cell by ejecting an electron from the floating gate of each memory cell. In this case, a data write operation is executed by applying a high voltage to a control gate of the memory cell and applying a low voltage to a drain region thereof. As a result, the electron is ejected from the floating gate into the drain region. A data erase operation in this case is executed by applying a high voltage to the control gate of the memory cell and applying a high voltage to the source region thereof. As a result, a high electric field is applied to a tunnel oxide film at an interface between the source region and the substrate. Thus, the electron existing in the floating gate is ejected from the floating gate into the source region. In an EEPROM, a write operation (program operation) and an erase operation (erase operation) are executed by a Fowler-Nordheim tunneling current. For this reason, the write operation (program operation) and 82157476af

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